

Silicon PNP Power Transistors

2SB1530

DESCRIPTION

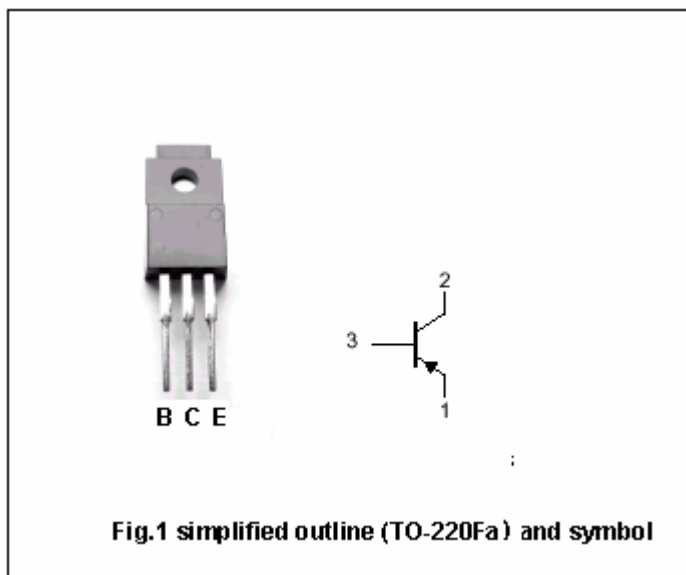
- With TO-220Fa package
- High V_{CEO}
- Complement to type 2SD2337

APPLICATIONS

- For low frequency power amplifier color TV vertical deflection output applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-200	V
V_{CEO}	Collector-emitter voltage	Open base	-150	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current (DC)		-2	A
I_{CM}	Collector current-Peak		-5	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	20	W
		$T_a=25^\circ\text{C}$	1.5	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-45~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA, R _{BE} =∞	-150			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-5mA, I _C =0	-6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-500mA; I _B =-50mA			-3.0	V
V _{BE}	Base-emitter on voltage	I _C =-50mA; V _{CE} =-4V			-1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-120V; I _E =0			-1	μA
h _{FE-1}	DC current gain	I _C =-50mA; V _{CE} =-4V	60		200	
h _{FE-2}	DC current gain	I _C =-500mA; V _{CE} =-10V	60			

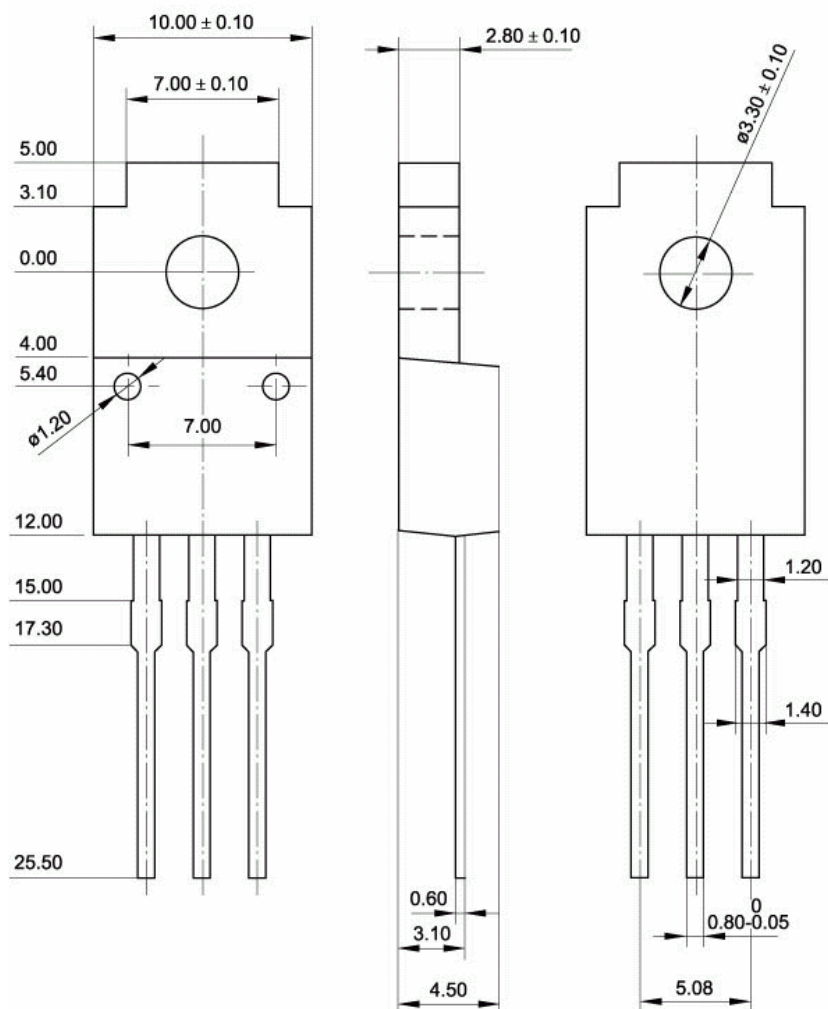
◆ h_{FE-1} Classifications

B	C
60-120	100-200

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PACKAGE OUTLINE

Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)